

NSH160N25D



N-Channel Enhanced Shielded Gate Trench Power MOSFET

Voltage: 250 Volts

Current: 93 Ampers

Package: TO-263

Features

- NH'S Advanced SGT Technology
- Low Reverse Transfer Capacitances
- Low Gate Charge For Low Switching Loss
- Excellent $Q_g \cdot R_{ds(on)}$ Product(FOM)

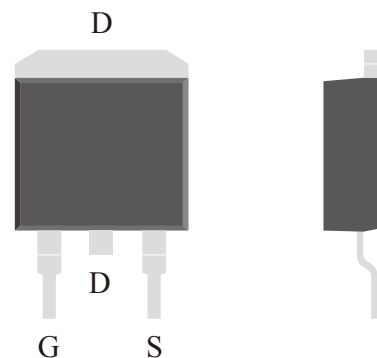
Typical Applications

- Synchronous Rectification
- High-Frequency Circuits
- The Motor Drives
- Automotive Electronics

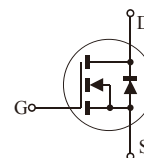
Product Summary

V _{DS} Min.@T _j	250	V
I _D Min.@T _a	93	A
R _{DS(ON)} (TYP)@10V	15.5	mΩ

Diagram:



Polarity:



***100% UIS TESTED**

***100% ΔV_{DS} TESTED**

Absolute Maximum Ratings (T_a=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	250	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 1)	T _a = 25 ℃	I _D	93	A
	T _a = 100 ℃		84	
Drain Current-Pulse (Note 1)	T _j < 175 ℃	I _{DM}	372	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25℃	T _a = 25 ℃	P _D	429	W
	T _a = 100 ℃		214	
Derating Factor		D _F	2.86	W/℃
Avalanche Current,Single Pulse (Note 1)	L= 0.4 mH	I _{AS}	30	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.17	L= 0.4 mH I _{AS} = 30 A,R _G = 10.0 Ω Starting T _j =25 ℃,V _G = 10.0 V	E _{AS}	180	mJ

Thermal Characteristics (T_a=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 175	℃
Storage Temperature Range		T _{STD}	-55 to 175	℃
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With T _a =25℃	R _{θJA}	60	℃/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 1 in2 FR-4 Board With 2oz. Copper	R _{θJC}	0.35	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig. 14).

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=250uA	BV _{DSS}	250	--	--	V
Bvdss Temperature Coefficient	ID=250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.24	--	V/℃
Drain-Source Leakage Current	VDS= 250 V,VGS=0V	I _{DSS}	--	--	1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= 20.0 A,VDS= 5 V	g _{fs}	--	70	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=250uA	V _{GS(TH)}	2	3	4	V
Drain-Source On Resistance	ID= 20.0 A,VGS= 10.0 V	R _{DS(ON)}	--	15.5	22	mΩ
	ID= 20.0 A,VGS= 5.0 V		--	22.5	33	
Dynamic Characteristics						
Input Capacitance	VDS= 50 V	C _{iss}	--	4950	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	350	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	7	--	pF
Gate Resistance	VGS=0V,VDS=0V, Freq.=1MHz	R _g	--	3.7	--	Ω
Switching Paramters (Test Circuit & Waveform See Fig.15)						
Turn-On Delay Time	VDS= 50 V	t _{d(on)}	--	17	--	ns
Turn-On Rise Time	VGS= 10.0 V	t _r	--	22	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	40	--	ns
Turn-Off Rise Time	L= 0.4 mH	t _f	--	11	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.16)						
Total Gate Charge	VDS= 50 V	Q _g	--	58	--	nC
Gate-Source Charge	VGS= 10.0 V	Q _{gs}	--	18	--	nC
Gate-Drain Charge	ID= 20.0 A	Q _{gd}	--	6	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.18)						
Max. Diode Forward Cuurent		I _S	--	--	93.0	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	372	A
Diode Forward Voltage	ID= 20.0 A,VGS=0V	V _{SD}	--	0.7	1.2	V
Reverse Recovery Time	IS= 20.0 A,di/dt= 100 A/us	t _{rr}	--	168	--	ns
Reverse Recovery Charge	VGS= 0.0 V	Q _{rr}	--	840	--	nC
Reverse Recovery Current		I _{RRM}	--	10.0	--	A

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Typical Characteristics Curves

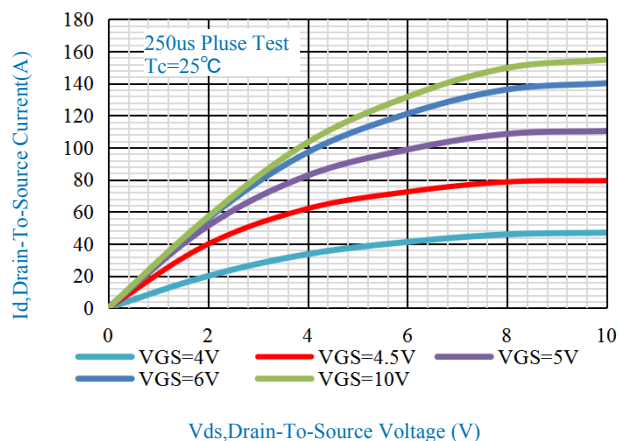


Fig.1-Output Characteristics

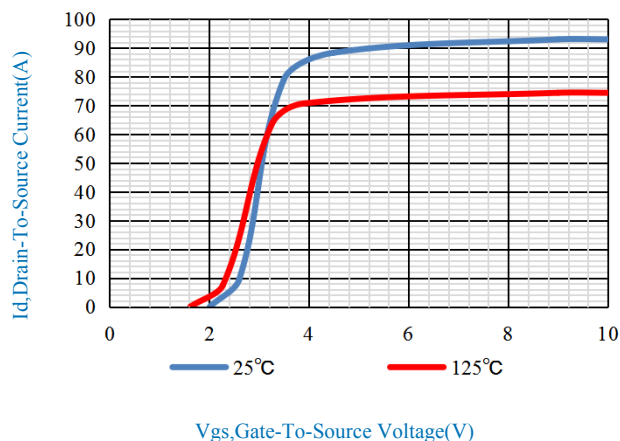


Fig.2-Transfer Characteristics

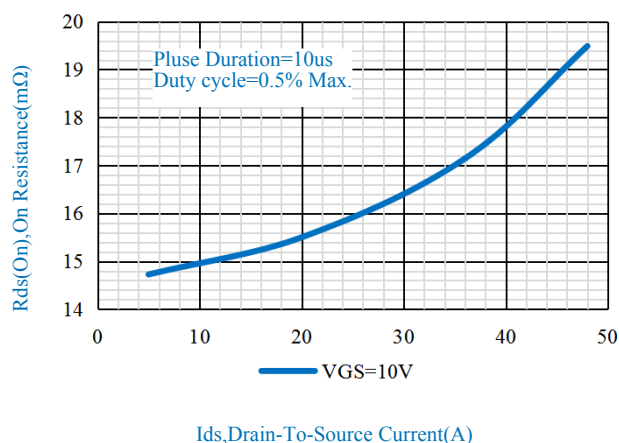


Fig.3-On Resistance Vs. Drain Current

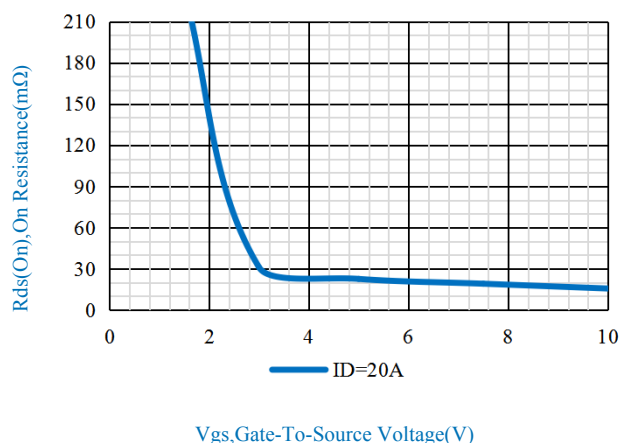


Fig.4-On Resistance Vs. Gate Source Voltage

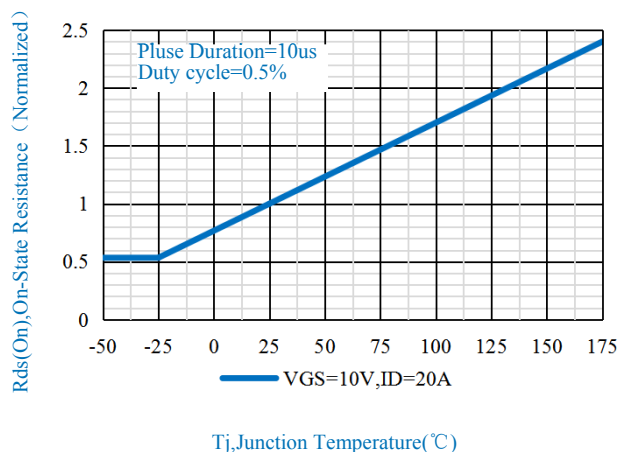


Fig.5-On Resistance Vs. Junction Temperature

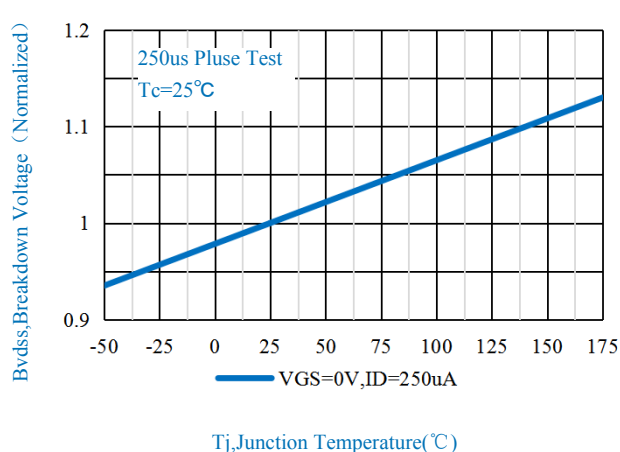


Fig.6-Breakdown Voltage Vs. Junction Temperature

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Typical Characteristics Curves

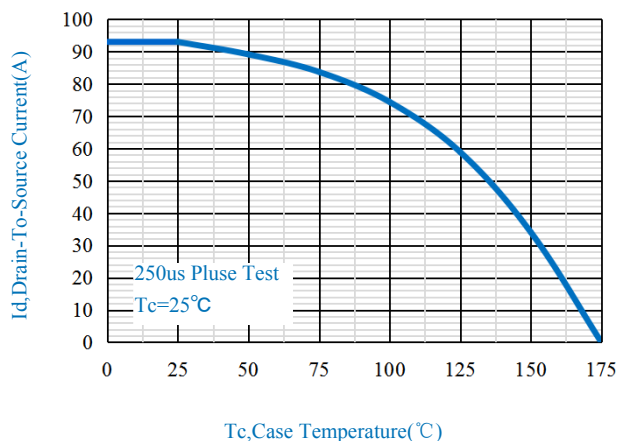


Fig.7-Maximum Continuous Drain Current Vs. Case Temperature

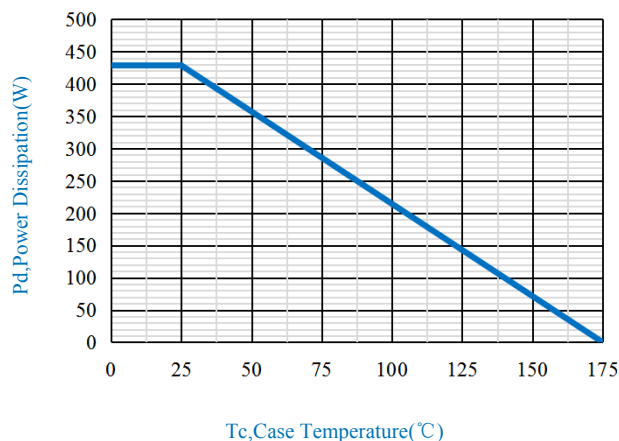


Fig.8-Maximum Power Dissipation Vs. Case Temperature

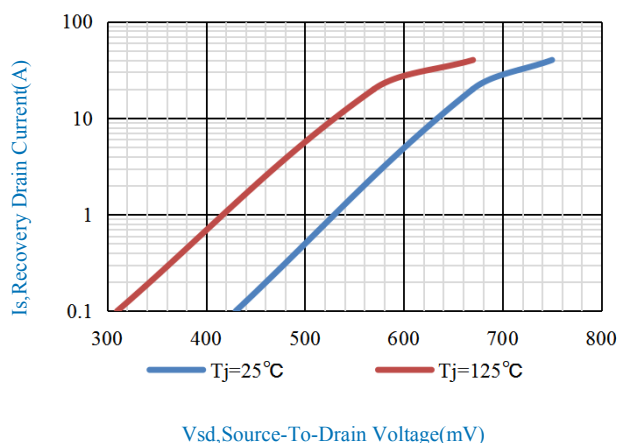


Fig.9-Source-To-Drain Diode Forward Voltage

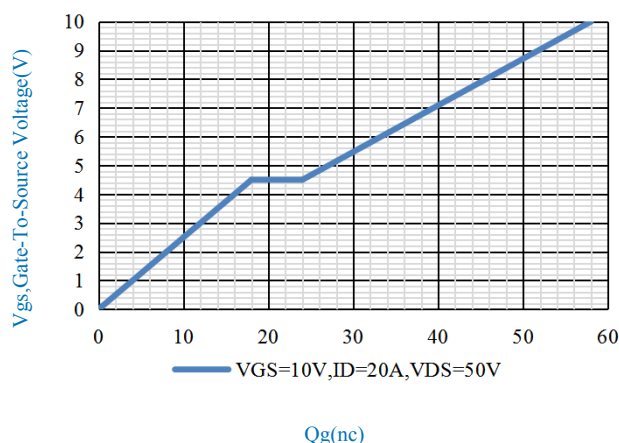


Fig.10-Gate Charge Waveform

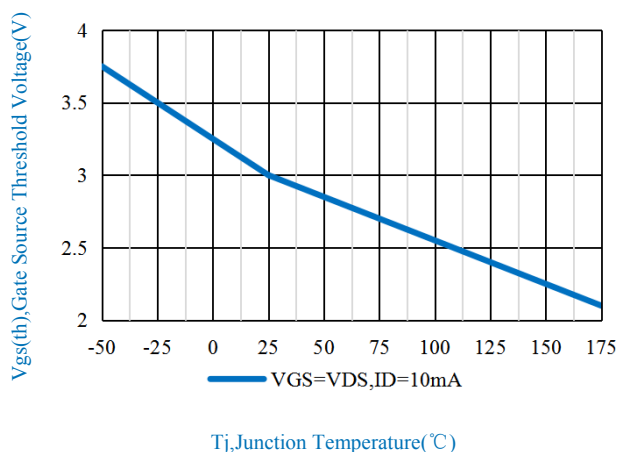


Fig.11-Gate Source Threshold Voltage Vs. Junction Temperature

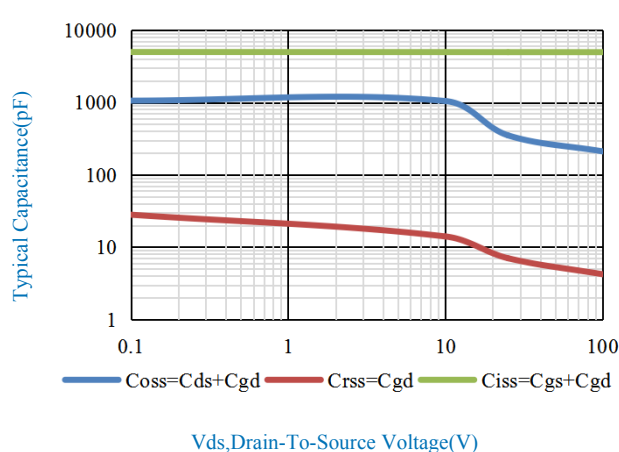


Fig.12-Typical Capacitance Vs. Drain-To-Source Voltage

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Typical Characteristics Curves

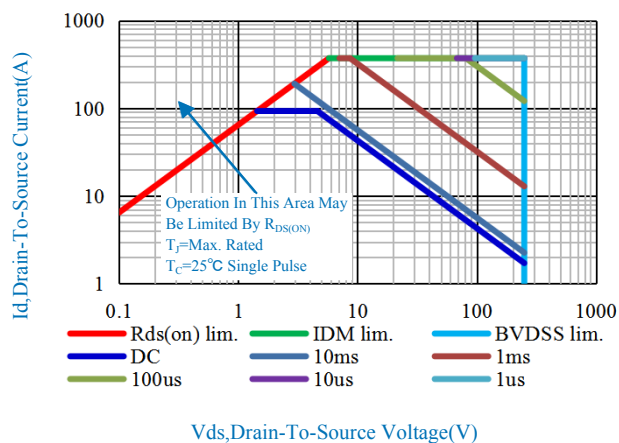


Fig.13-Maximum Safe Operating Area(SOA)

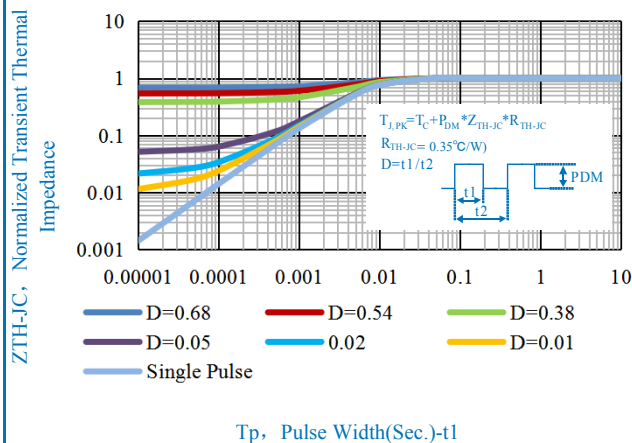


Fig.14- Normalized Maximum Transient Thermal Impedance Vs. Pulse Width

Test Circuit & Waveform

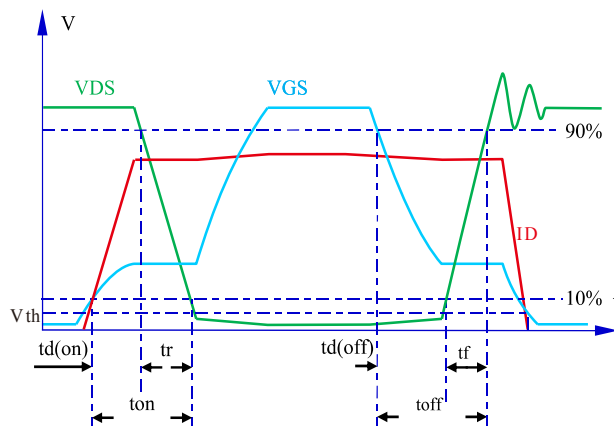
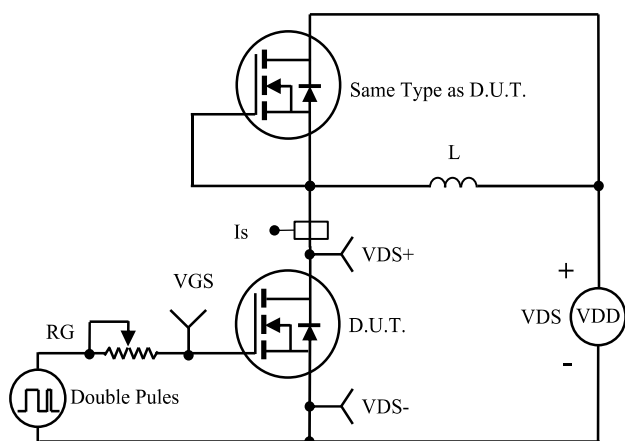


Fig.15- Inductive Switching Test Circuit & Waveform

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Test Circuit & Waveform

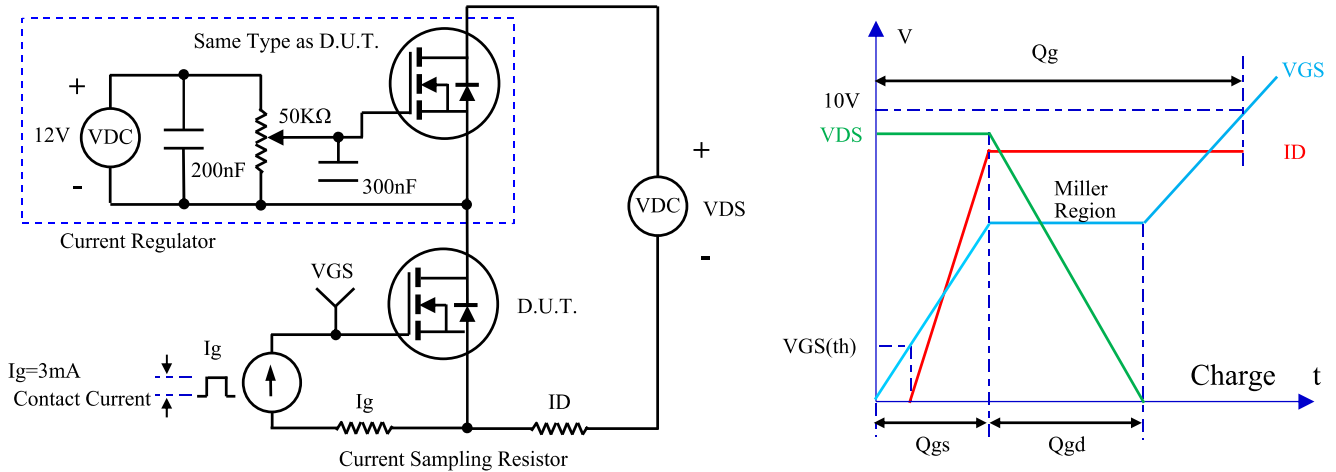


Fig.16-Gate Charge Test Circuit & Waveform

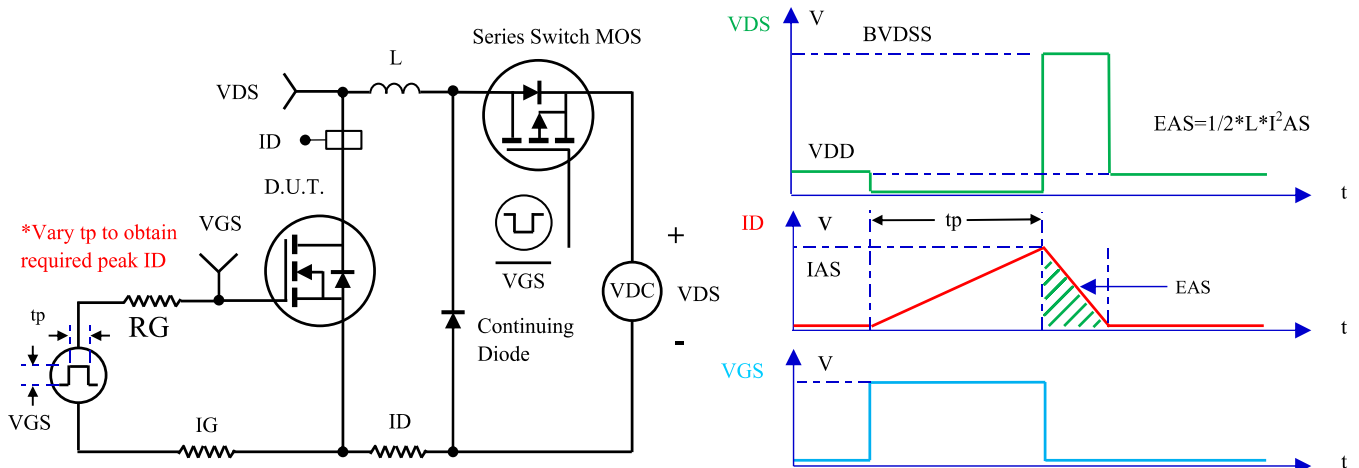


Fig.17- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

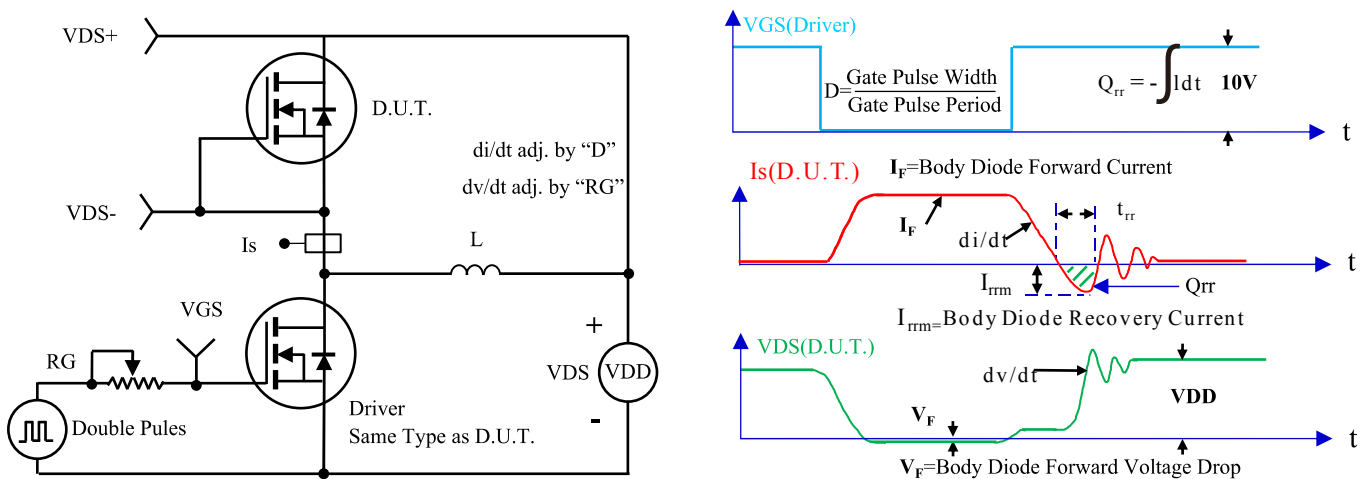


Fig.18- Diode Recovery Test Circuit & Waveform

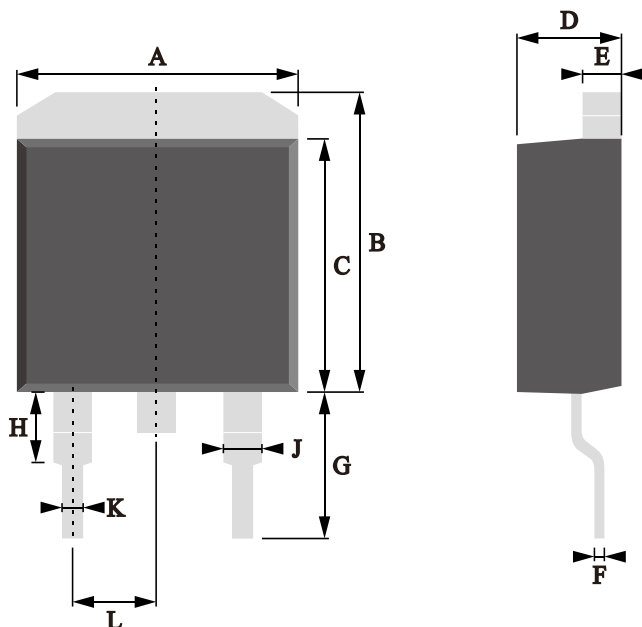
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OUTLINE DRAWINGS

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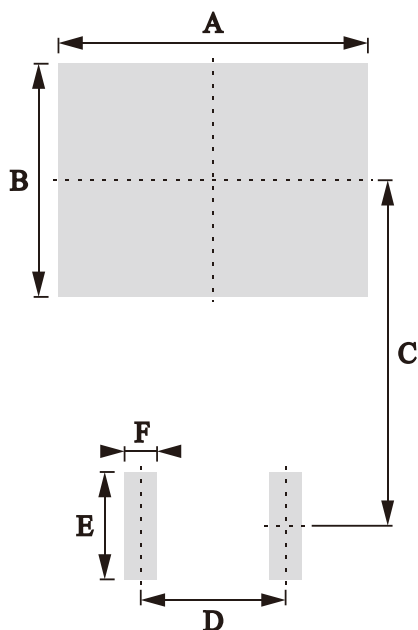


OUTLINE DIMENSIONS

Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.30	-	10.50	0.3661	-	0.4134
B	9.60	-	11.60	0.3780	-	0.4567
C	8.20	-	9.50	0.3228	-	0.3740
D	4.00	-	5.00	0.1575	-	0.1969
E	1.00	-	1.70	0.0394	-	0.0669
F	0.20	-	0.70	0.0079	-	0.0276
G	4.45	-	5.25	0.1752	-	0.2067
H	1.25	-	1.85	0.0492	-	0.0728
J	1.00	-	1.60	0.0394	-	0.0630
K	0.60	-	1.00	0.0236	-	0.0394
L	2.25	-	2.80	0.0886	-	0.1102

RECOMMENDED LAYOUT DRAWINGS

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OUTLINE DIMENSIONS

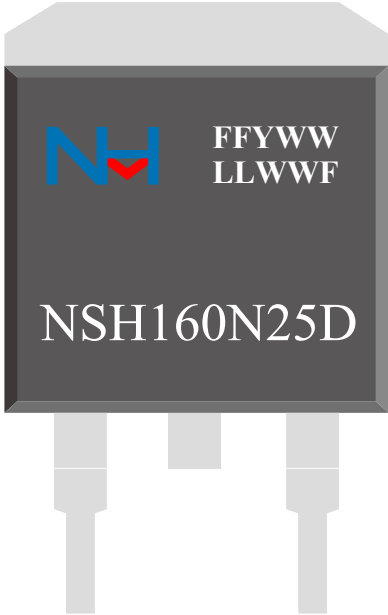
Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	10.86	-	-	0.4276	-
B	-	7.86	-	-	0.3094	-
C	-	11.64	-	-	0.4583	-
D	-	5.08	-	-	0.2000	-
E	-	3.62	-	-	0.1425	-
F	-	1.14	-	-	0.0449	-

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MARKING INFORMATION



MARKING INSTRUCTIONS

NH=Niuhang Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Inernal Code,According To Actual Changes
NSH160N25D=Model

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TO-263	P1	1.4331	13" Reel	800	800	4000
TO-263	P2	1.4331	13" Reel	800	800	4800

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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow

	Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
	Average ramp-up rate (T _{Smax} to T _P)	3°C/second max.	3°C/second max.
	Preheat-Temperature Min (T _{Smin}) -Temperature Max (T _{Smax}) -Time(t _{Smin} to t _{Smax})	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
	Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
	Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
	Time within 5°C of actual peak temperature (t _p)	10-30 seconds	20-40 seconds
	Ramp down rate	6°C/second max.	6°C/second max.
	Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2014-10-20	First Issue		
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